

Silicon PNP Power Transistors

2SA634

DESCRIPTION

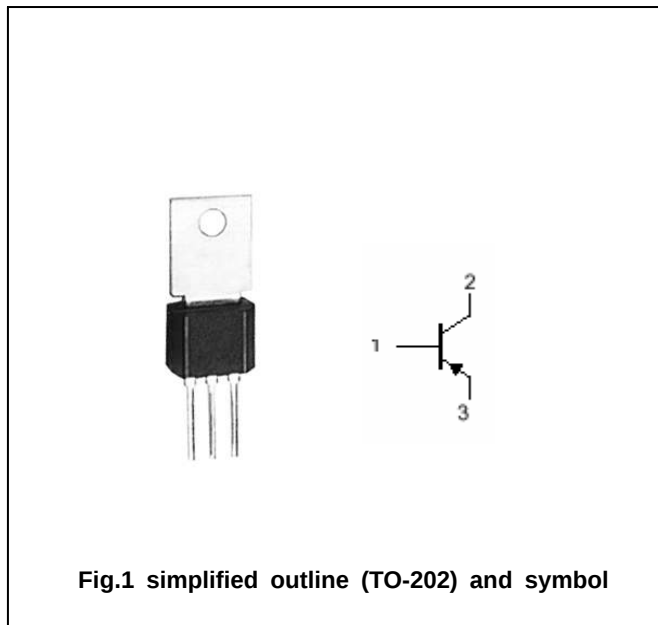
- With TO-202 package
- Complement to type 2SC1096
- High current capability

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3.0	A
I_{CM}	Collector current-peak		-6.0	A
I_B	Base current		-0.6	A
P_T	Total power dissipation	$T_a=25^\circ\text{C}$	1.2	W
		$T_c=25^\circ\text{C}$	10	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3.0\text{A}; I_B=-0.3\text{A}$			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-3.0\text{A}; I_B=-0.3\text{A}$			-2.0	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10\text{mA}; I_B=0$	-30			V
h_{FE-1}	DC current gain	$I_C=-20\text{mA}; V_{CE}=-5\text{V}$	20			
h_{FE-2}	DC current gain	$I_C=-1\text{A}; V_{CE}=-5\text{V}$	40		250	
I_{CBO}	Collector cut-off current	$V_{CB}=-30\text{V}; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3\text{V}; I_C=0$			-1.0	μA
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10\text{V}; f=1\text{MHz}$		75		pF
f_T	Transition frequency	$I_C=-0.1\text{A}; V_{CE}=-5\text{V}$		55		MHz

◆ h_{FE-2} Classifications

N	M	L	K
40-60	50-100	80-160	120-250

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PACKAGE OUTLINE

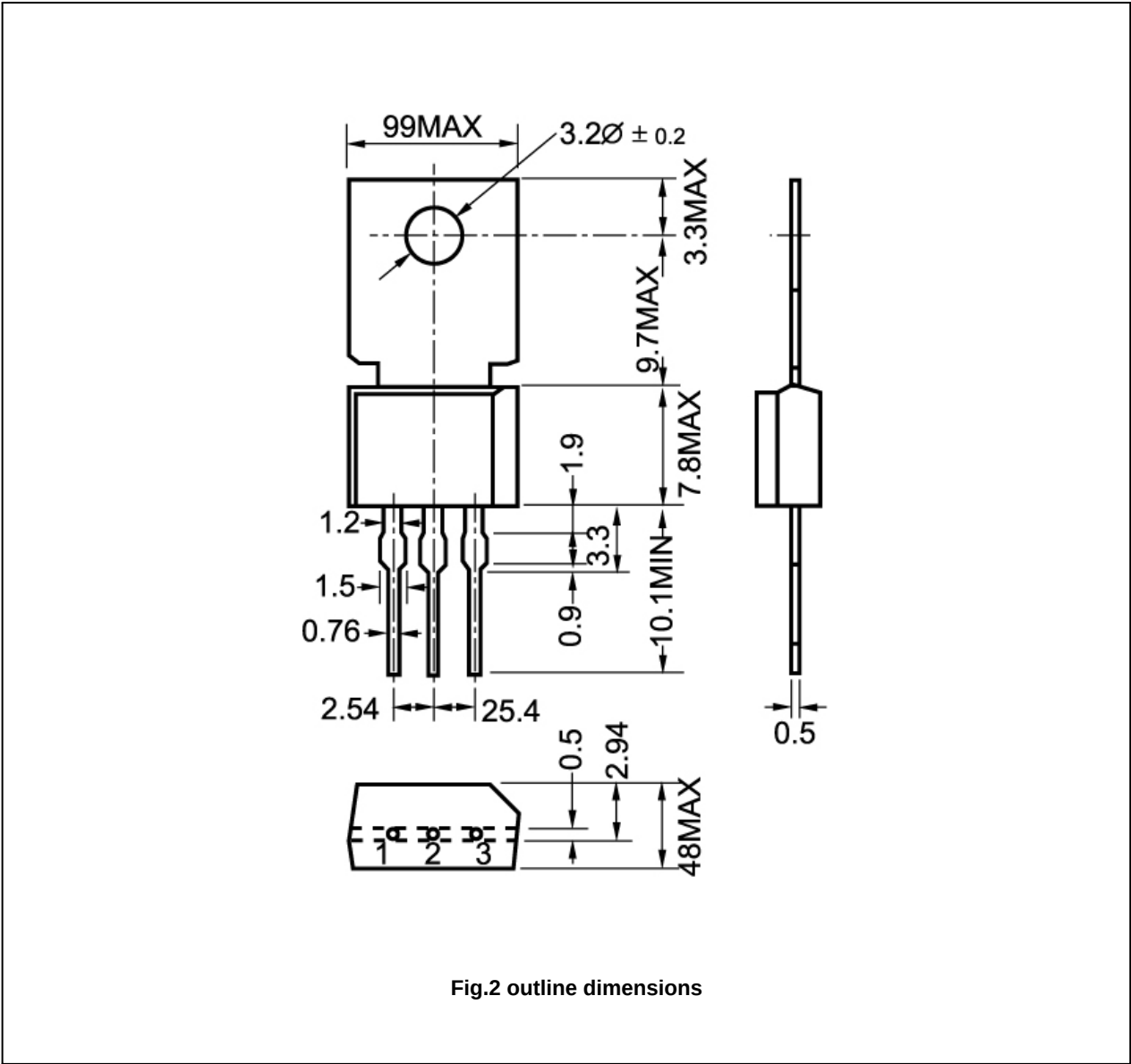


Fig.2 outline dimensions